



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

OHTAKE, Fumio et al.

Corres. and Mail

Group Art Unit: 2814

Serial No.: 09/749,590

BOX AF

Examiner: MAI, Anh D.

Filed: December 28, 2000

P.T.O. Confirmation No.: 4831

For: **SEMICONDUCTOR DEVICE HAVING GATE ELECTRODES WITH POLYMETAL
STRUCTURE OF POLYCRYSTALLINE SILICON FILMS AND METAL FILMS** (as
amended)

RESPONSE UNDER 37 CFR §1.116

- EXPEDITED RESPONSE -

GROUP ART UNIT 2814

BOX AF

Commissioner for Patents
Washington, D.C. 20231

March 11, 2003

Sir:

In response to the Office Action dated December 16, 2002, please amend the above-identified
application as follows:

IN THE CLAIMS:

Please **CANCEL** claims 18 and 19 without prejudice or disclaimer.

Please **AMEND** claims as follows:

1. (Twice Amended) A semiconductor device comprising:

a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and

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J. Antis

4/16/03

C.P.

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